Ordering number : EN6446D

MCH6603

P-Channel Power MOSFET
−50V, −0.14A, 23Ω, Dual MCPH6

ON Semiconductor®
http://onsemi.com

Features

- Low ON-resistance
- Ultrahigh-speed switching
- 1.5V drive
- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting
- Halogen free conplaiance

Specifications

Absolute Maximum Ratings at Ta=25°C

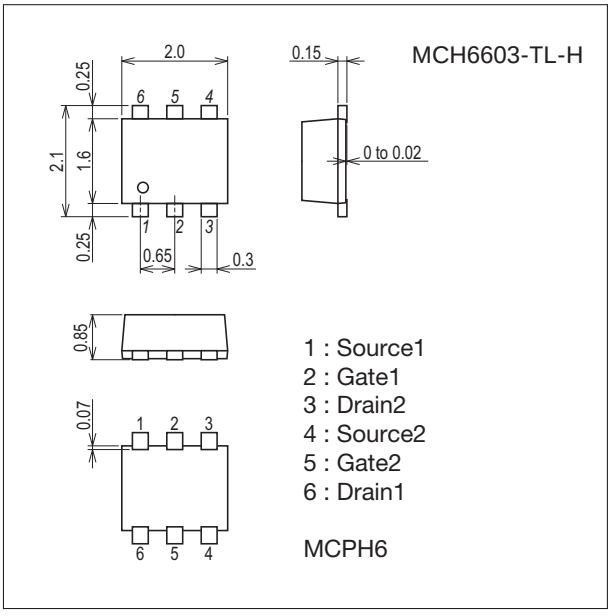
Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	V_{DSS}		−50	V
Gate to Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		−0.14	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−0.56	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm)1unit	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.
* Machine Model

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

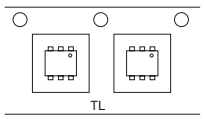
unit : mm (typ)
7022A-006



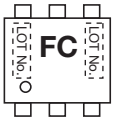
Product & Package Information

- Package : MCPH6
- JEITA, JEDEC : SC-88, SC-70-6, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

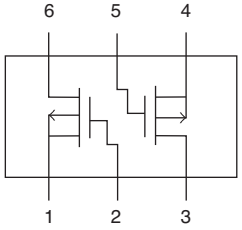
Packing Type : TL



Marking



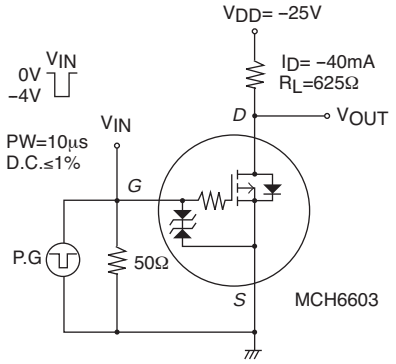
Electrical Connection



Electrical Characteristics at Ta=25°C

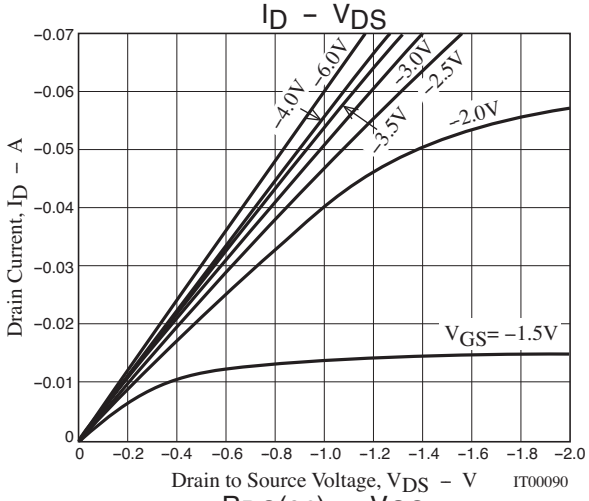
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−50			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−50V, V_{GS}=0V			−1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=−10V, I_D=−100μA	−0.4		−1.4	V
Forward Transfer Admittance	| yfs |	V_{DS}=−10V, I_D=−40mA	70	110		mS
Static Drain to Source On-State Resistance	R_{DS}(on)1	I_D=−40mA, V_{GS}=−4V		18	23	Ω
	R_{DS}(on)2	I_D=−20mA, V_{GS}=−2.5V		20	28	Ω
	R_{DS}(on)3	I_D=−5mA, V_{GS}=−1.5V		30	60	Ω
Input Capacitance	Ciss	V_{DS}=−10V, f=1MHz		7.4		pF
Output Capacitance	Coss			4.2		pF
Reverse Transfer Capacitance	Crss			1.3		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		20		ns
Rise Time	t_r			35		ns
Turn-OFF Delay Time	t_d(off)			160		ns
Fall Time	t_f			150		ns
Total Gate Charge	Qg	V_{DS}=−10V, V_{GS}=−10V, I_D=−70mA		1.40		nC
Gate to Source Charge	Qgs			0.16		nC
Gate to Drain “Miller” Charge	Qgd			0.23		nC
Diode Forward Voltage	V_{SD}	I_S=−70mA, V_{GS}=0V		−0.85	−1.2	V

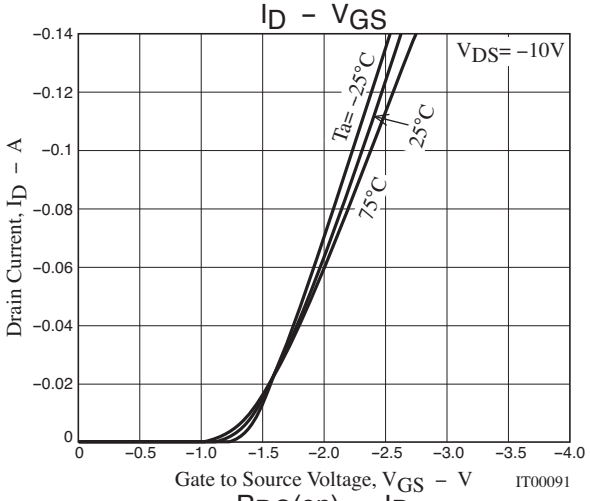
Switching Time Test Circuit

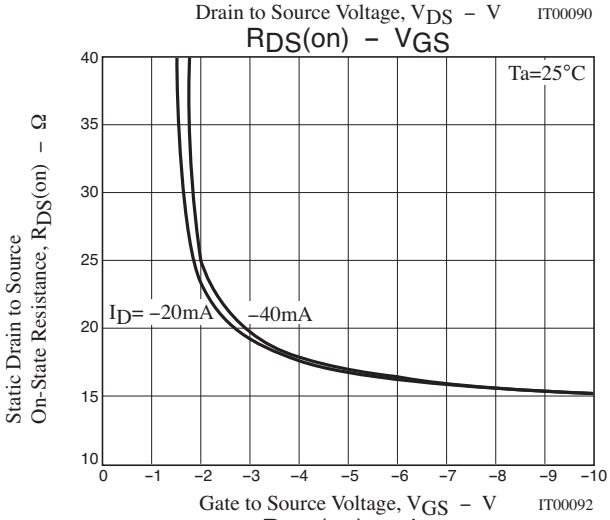


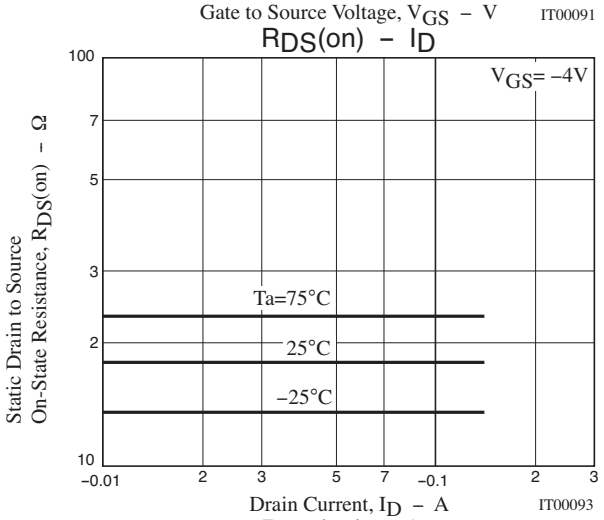
Ordering Information

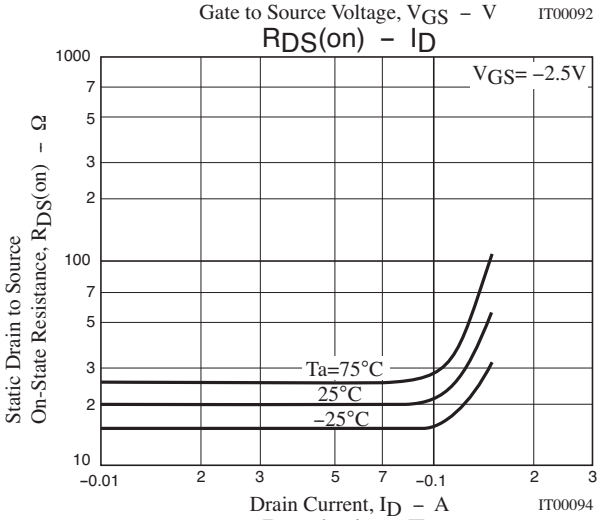
Device	Package	Shipping	memo
MCH6603-TL-H	MCPH6	3,000pcs./reel	Pb-Free and Halogen Free

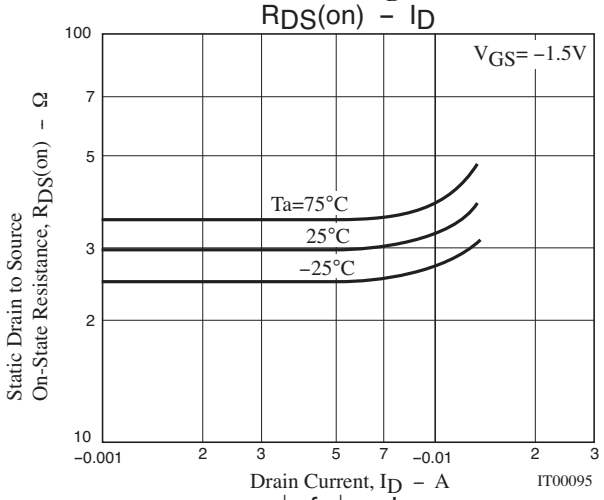


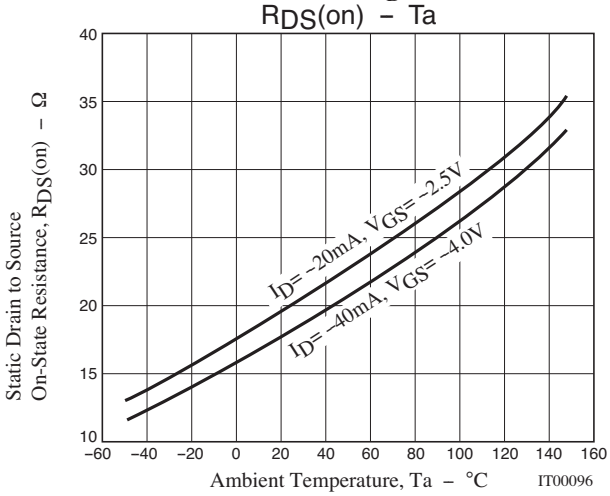


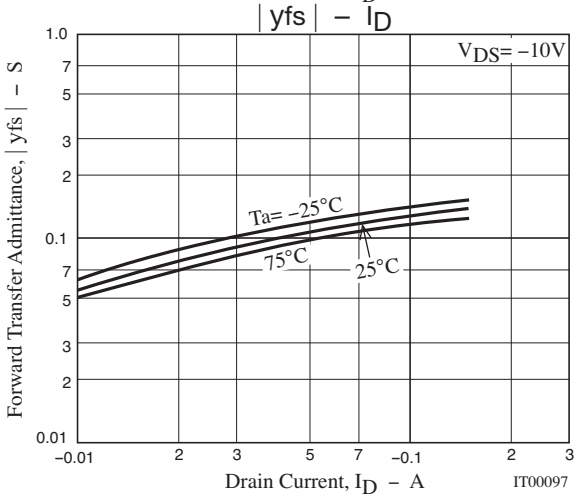


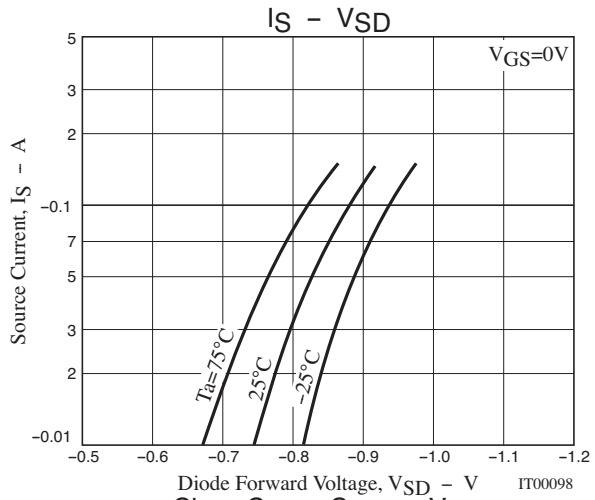


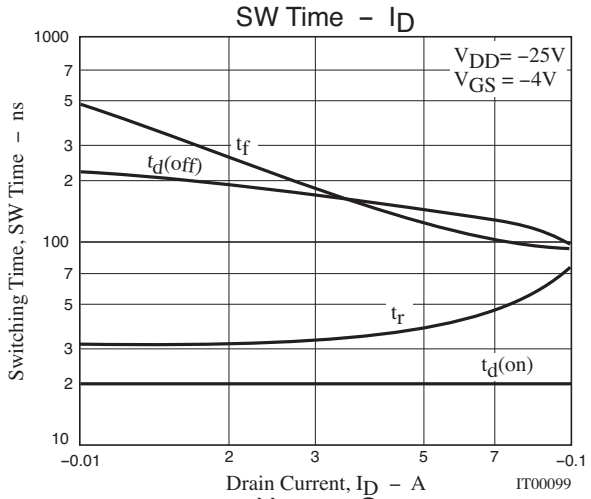


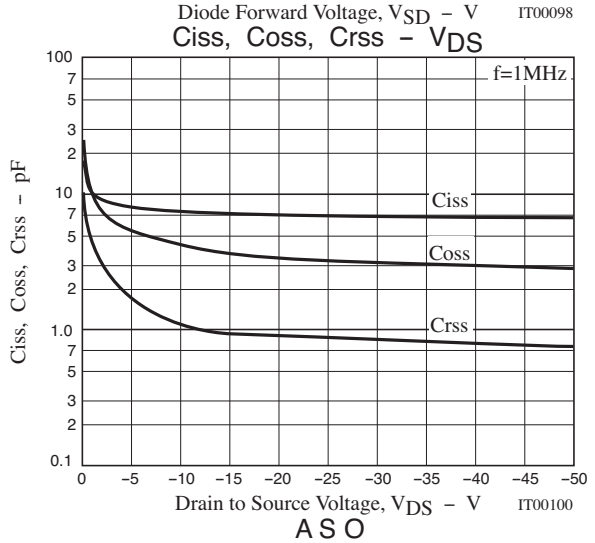


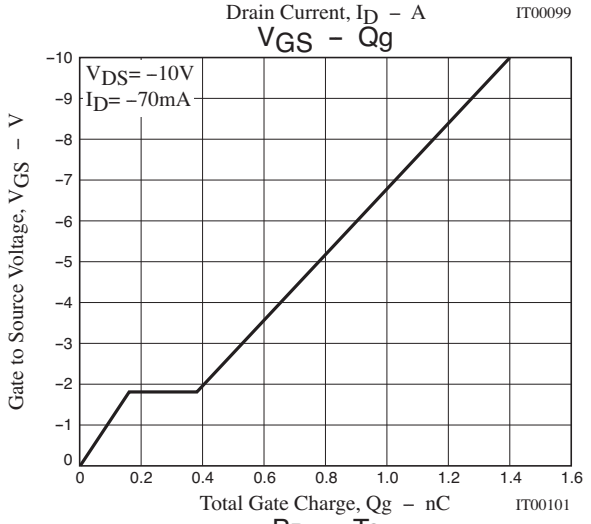


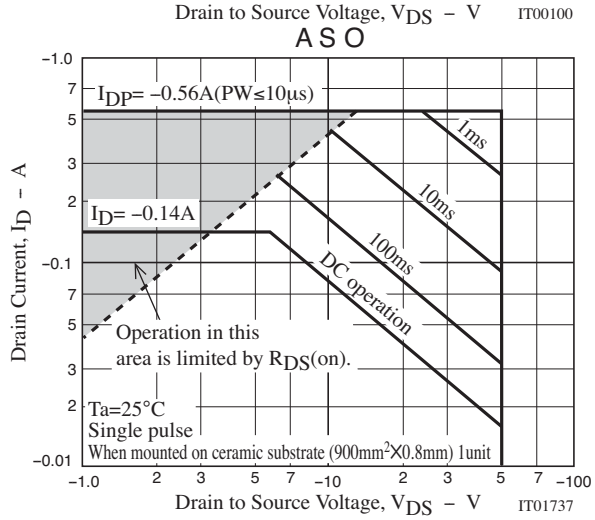


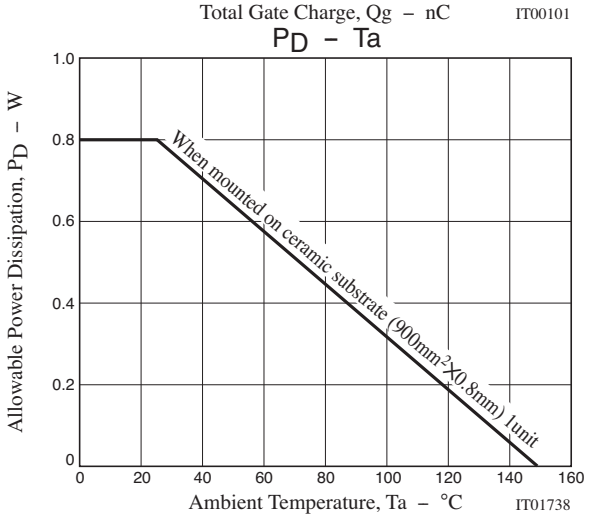






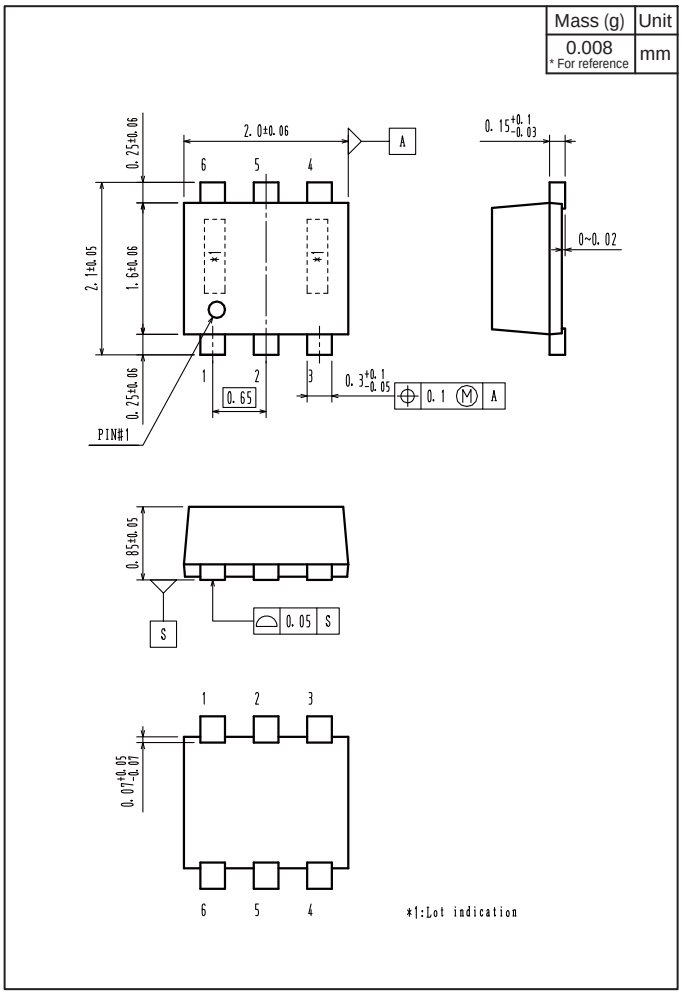




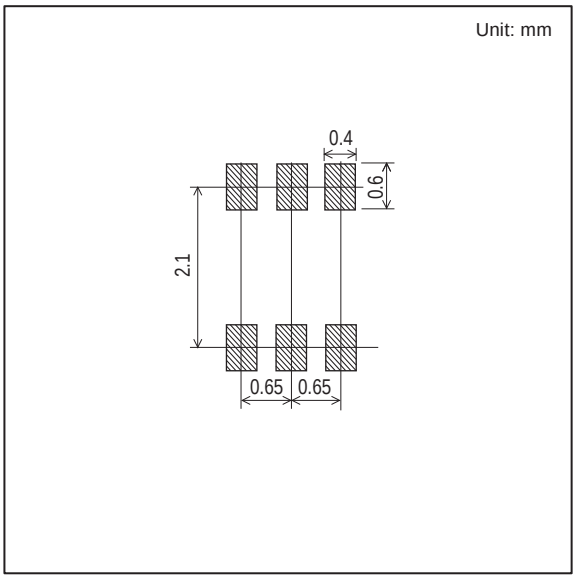


Outline Drawing

MCH6603-TL-H



Land Pattern Example



Note on usage : Since the MCH6603 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.